

PTB 20134

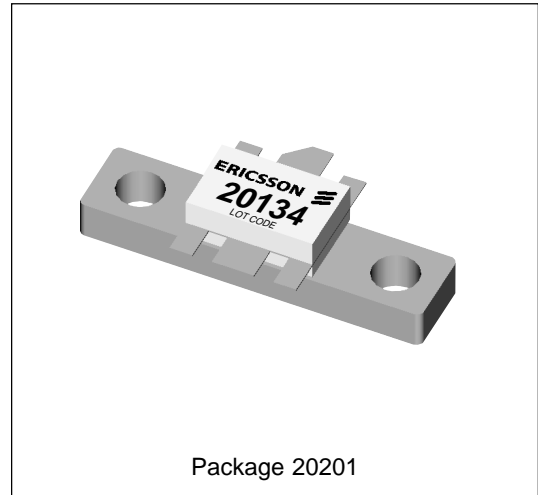
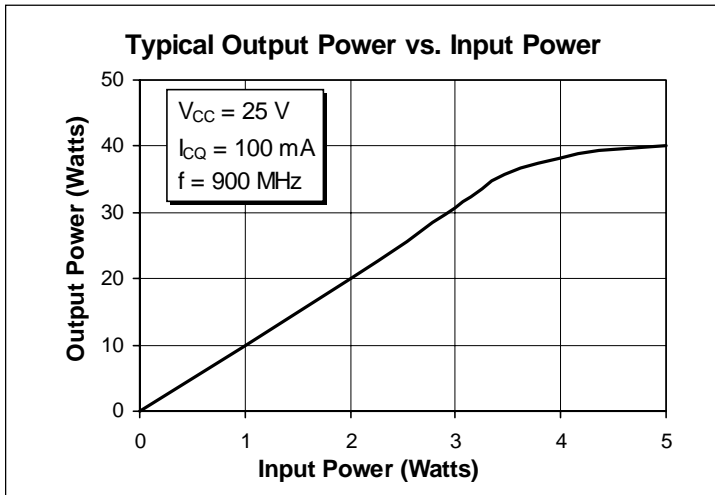
30 Watts, 860–900 MHz

Cellular Radio RF Power Transistor

Description

The 20134 is a class AB, NPN, common emitter RF power transistor intended for 25 Vdc operation from 860 to 900 MHz. Rated at 30 watts minimum output power, it may be used for both CW and PEP applications. Ion implantation, nitride surface passivation and gold metallization are used to ensure excellent device reliability. 100% lot traceability is standard.

- 30 Watts, 860–900 MHz
- Class AB Characteristics
- 50% Min Collector Efficiency at 30 Watts
- Gold Metallization
- Silicon Nitride Passivated



Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CER}	40	Vdc
Collector-Base Voltage	V_{CBO}	50	Vdc
Emitter-Base Voltage (collector open)	V_{EBO}	4.0	Vdc
Collector Current (continuous)	I_C	8.0	Adc
Total Device Dissipation at $T_{flange} = 25^{\circ}C$ Above $25^{\circ}C$ derate by	P_D	80 0.45	Watts W/ $^{\circ}C$
Storage Temperature Range	T_{STG}	-40 to +150	$^{\circ}C$
Thermal Resistance ($T_{flange} = 70^{\circ}C$)	$R_{\theta JC}$	2.2	$^{\circ}C/W$

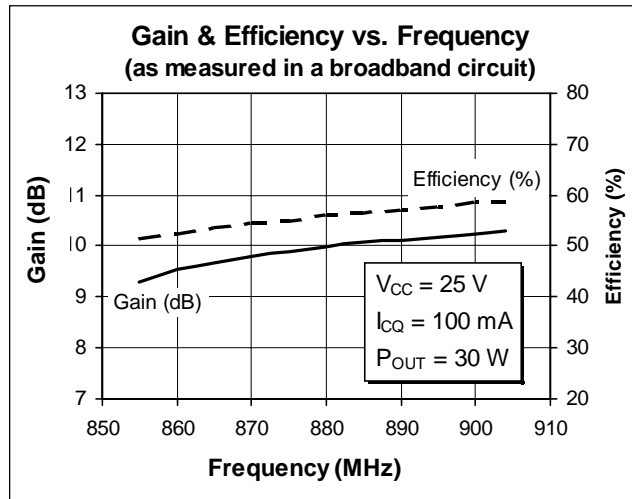
Electrical Characteristics (100% Tested)

Characteristic	Conditions	Symbol	Min	Typ	Max	Units
Breakdown Voltage C to E	$I_B = 0\text{ A}, I_C = 100\text{ mA}$	$V_{(BR)CEO}$	25	30	—	Volts
Breakdown Voltage C to E	$V_{BE} = 0\text{ V}, I_C = 100\text{ mA}$	$V_{(BR)CES}$	55	70	—	Volts
Breakdown Voltage E to B	$I_C = 0\text{ A}, I_E = 5\text{ mA}$	$V_{(BR)EBO}$	3.5	5	—	Volts
DC Current Gain	$V_{CE} = 5\text{ V}, I_C = 1\text{ A}$	h_{FE}	20	50	100	—

RF Specifications (100% Tested)

Characteristic	Symbol	Min	Typ	Max	Units
Gain ($V_{CC} = 25\text{ Vdc}, P_{out} = 30\text{ W}, I_{CQ} = 100\text{ mA}, f = 900\text{ MHz}$)	G_{pe}	8	9.5	—	dB
Collector Efficiency ($V_{CC} = 25\text{ Vdc}, P_{out} = 30\text{ W}, I_{CQ} = 100\text{ mA}, f = 900\text{ MHz}$)	η_C	50	—	—	%
Intermodulation Distortion ($V_{CC} = 25\text{ Vdc}, P_{out} = 30\text{ W(PEP)}, I_{CQ} = 100\text{ mA}, f = 900\text{ MHz}, \Delta f = 1\text{ MHz}$)	IMD	—	-30	—	dBc
Load Mismatch Tolerance ($V_{CC} = 25\text{ Vdc}, P_{out} = 30\text{ W}, I_{CQ} = 100\text{ mA}, f = 900\text{ MHz}$ —all phase angles at frequency of test)	Ψ	—	—	30:1	—

Typical Performance



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